

Internal Amplification $Ge(GeIA)$

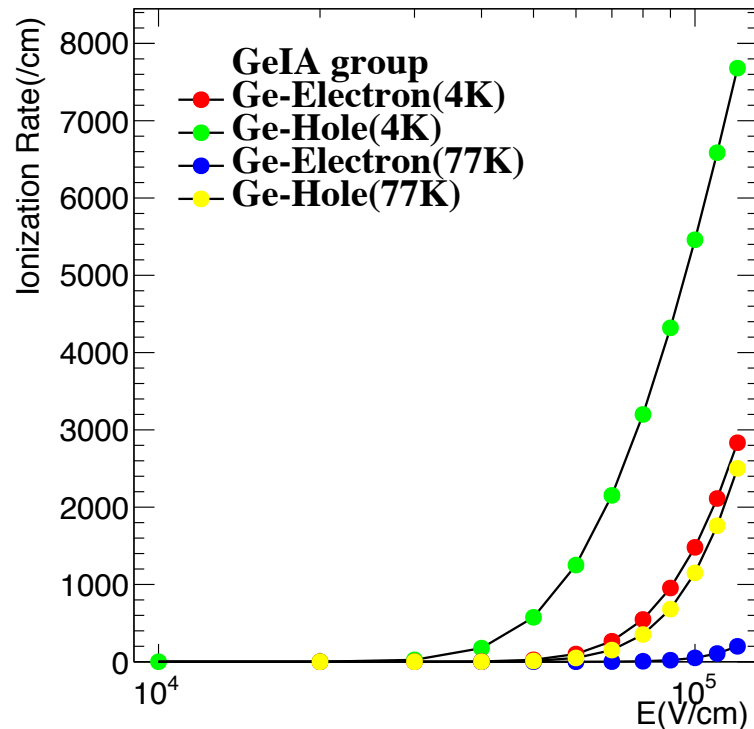
Theory of predicting the necessary gain

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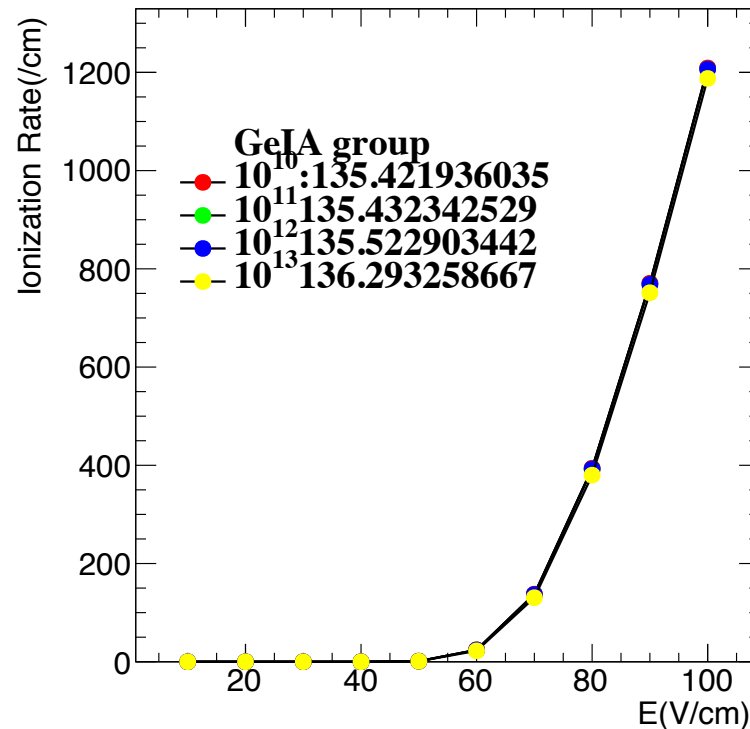
The reminder of the previous results

- At the first place, the ionization rates of electron and hole were predicted by some of the formulae:

Signal(Ge)



Signal(Impurities)



Ionization rate

→ Give us the “Gain” in the end.

→ Great! But what’s the next?

→ Debut of our “BKG”!!

→ Umm...It seems complicated!

→ Let me map out the blueprint first!

Three steps



Ionization rate
Gain(E,T)



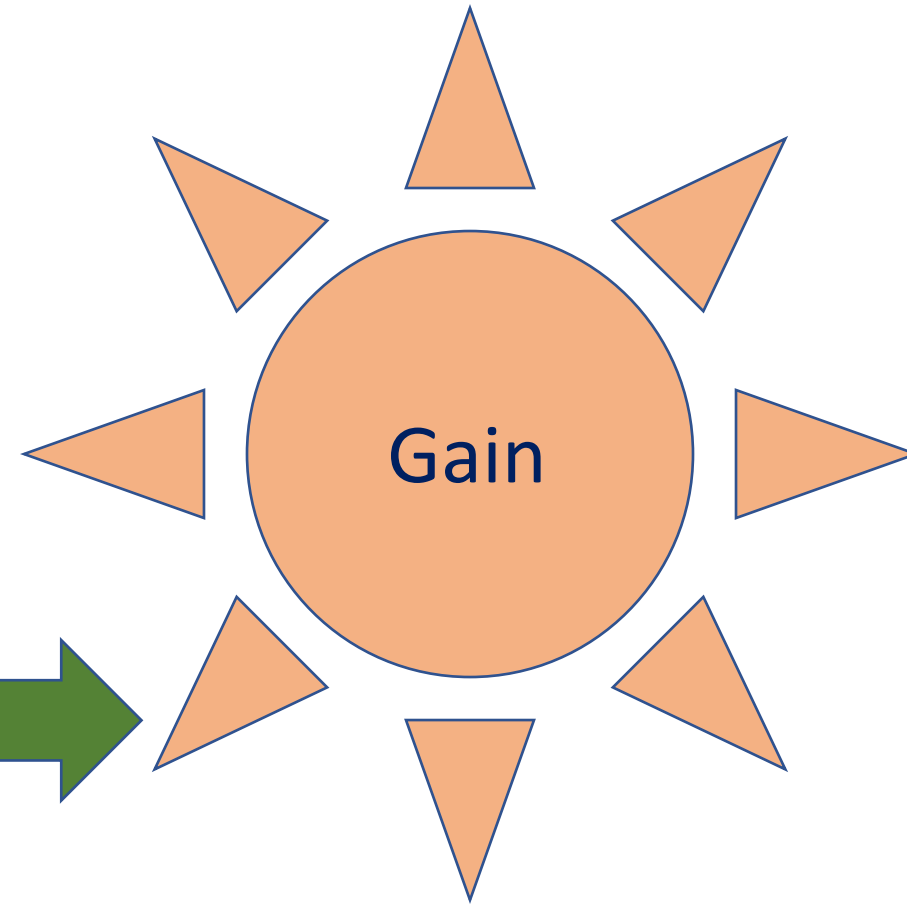
Know our predicted gain for signal
Under the certain T and E



Theory of BKG
Signal threshold



Know the threshold of the signal
(Signal → Gain)
Predicted by BKG (Theory)



Type of the detector?
Temperature?
Electric field?

Raw/Observable



S

B



$S * G$

$B * G$

$$(SIG) > (3 * \text{sigma of BKG})$$

$$(S * G) > 3 * \sqrt{(B * G)}$$

$$S > \frac{3 * \sqrt{(B * G)}}{G}$$

Various thresholds (Given the dark matter energy) → All can be predicted.

Confirm the circumstance

	G	S(GS)	B(GB)	Threshold
(1)USD	1	1(1)	1(1)	3
(2)China-THU	100	1(100)	100(10000)	3

$$(SIG) > (3 * \text{sigma of BKG})$$

$$(S * G) > 3 * \sqrt{(B * G)}$$

$$S > \frac{3 * \sqrt{(B * G)}}{G}$$

Purpose of this study

- *The important issue:
- Can we predict “the necessary gain” by the signal we expect?
- Next step:
- Find out the right BKG and find out the right threshold plots.
- ➔ Then, we can apply it on our detector
- ➔ Even design the different type of the detector compared with other people.